

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ $T_A = 25^\circ C$
20V	5.5Ω @ $V_{GS} = -4.5V$	-200mA
	11.5Ω @ $V_{GS} = -1.8V$	-140mA

## Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power management functions

## Features and Benefits

- P-Channel MOSFET
- Low On-Resistance
  - 5.5Ω @ -4.5V
  - 7.5Ω @ -2.5V
  - 11.5Ω @ -1.8V
  - 17.5Ω @ -1.5V
- Very Low Gate Threshold Voltage  $V_{GS(TH)}$ , 1.15V max
- Low Input Capacitance
- Fast Switching Speed
- Ultra-Small Surfaced Mount Package
- Ultra-low package profile, 0.4mm maximum package height
- **ESD Protected Gate**
- **Lead, Halogen, and Antimony Free, RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

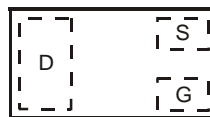
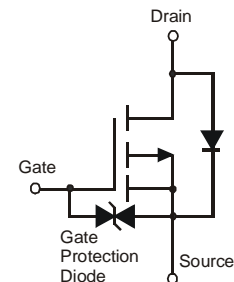
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)



X2-DFN1006-3



Bottom View


 Top View  
Internal Schematic


Equivalent Circuit

## Ordering Information (Note 3)

Part Number	Case	Packaging
DMP210DUFB4-7	X2-DFN1006-3	3,000/Tape & Reel
DMP210DUFB4-7B	X2-DFN1006-3	10,000/Tape & Reel

- Notes:
1. No purposefully added lead. Halogen and Antimony Free.
  2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
  3. For packaging details, go to our website at <http://www.diodes.com>.

## Marking Information

DMP210DUFB4-7


 Top View  
Dot Denotes  
Drain Side

DMP210DUFB4-7B


 Top View  
Bar Denotes Gate  
and Source Side

N1 = Product Type Marking Code

**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	-20	V
Gate-Source Voltage			$V_{GSS}$	$\pm 10$	V
Continuous Drain Current (Note 4) $V_{GS} = -4.5\text{V}$	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	-200	mA
		$T_A = 70^\circ\text{C}$		-160	
Continuous Drain Current (Note 4) $V_{GS} = -1.8\text{V}$	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	-140	mA
		$T_A = 70^\circ\text{C}$		-110	
Pulsed Drain Current			$I_{DM}$	-600	mA

**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	$P_D$	350	mW
Thermal Resistance, Junction to Ambient (Note 4)	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 5)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-20	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	-100	nA	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$ $V_{DS} = -5.0\text{V}, V_{GS} = 0\text{V}$
		—	—	-50	nA	
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 5.0\text{V}, V_{DS} = 0\text{V}$ $V_{GS} = \pm 8.0\text{V}, V_{DS} = 0\text{V}$ $V_{GS} = \pm 10.0\text{V}, V_{DS} = 0\text{V}$
		—	—	$\pm 1$	$\mu\text{A}$	
		—	—	$\pm 10$	$\mu\text{A}$	
<b>ON CHARACTERISTICS (Note 5)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-0.45	—	-1.15	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	5.5	$\Omega$	$V_{GS} = -4.5\text{V}, I_D = -100\text{mA}$
		—	—	7.5		$V_{GS} = -2.5\text{V}, I_D = -50\text{mA}$
		—	—	11.5		$V_{GS} = -1.8\text{V}, I_D = -20\text{mA}$
		—	—	17.5		$V_{GS} = -1.5\text{V}, I_D = -10\text{mA}$
		—	20	—		$V_{GS} = -1.2\text{V}, I_D = -10\text{mA}$
Forward Transfer Admittance	$ Y_{fs} $	150	200	—	mS	$V_{DS} = -10\text{V}, I_D = -200\text{mA}$
Diode Forward Voltage (Note 5)	$V_{SD}$	-0.5	—	-1.2	V	$V_{GS} = 0\text{V}, I_S = -115\text{mA}$
<b>DYNAMIC CHARACTERISTICS (Note 6)</b>						
Input Capacitance	$C_{ISS}$	—	13.72	175	pF	$V_{DS} = -15\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{OSS}$	—	4.01	30	pF	
Reverse Transfer Capacitance	$C_{RSS}$	—	2.34	20	pF	
<b>SWITCHING CHARACTERISTICS (Note 6)</b>						
Turn-On Delay Time	$t_{d(on)}$	—	7.7	—	ns	$V_{GS} = -4.5\text{V}, V_{DD} = -15\text{V}$ $I_D = -180\text{mA}, R_G = 2.0\Omega$
Rise Time	$t_r$	—	19.3	—		
Turn-Off Delay Time	$t_{d(off)}$	—	25.9	—		
Fall Time	$t_f$	—	31.5	—		

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

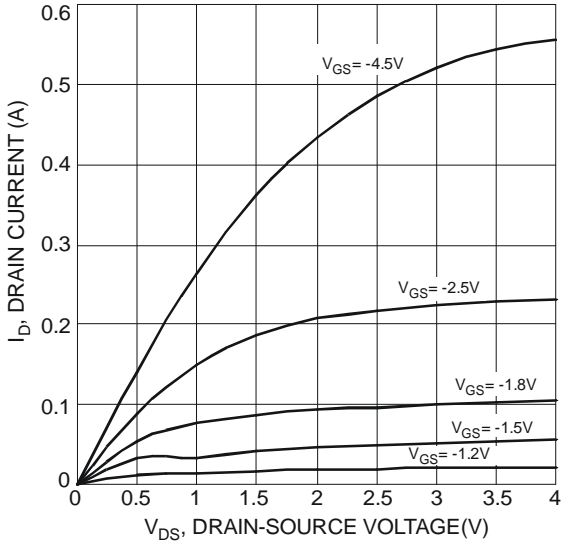


Fig. 1 Typical Output Characteristics

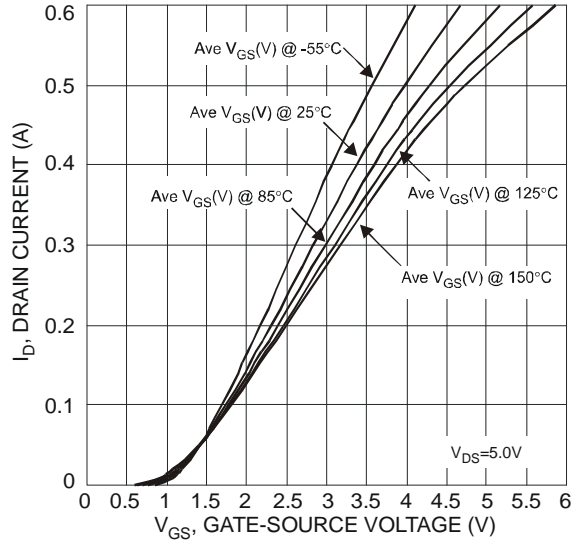


Fig. 2 Typical Transfer Characteristics

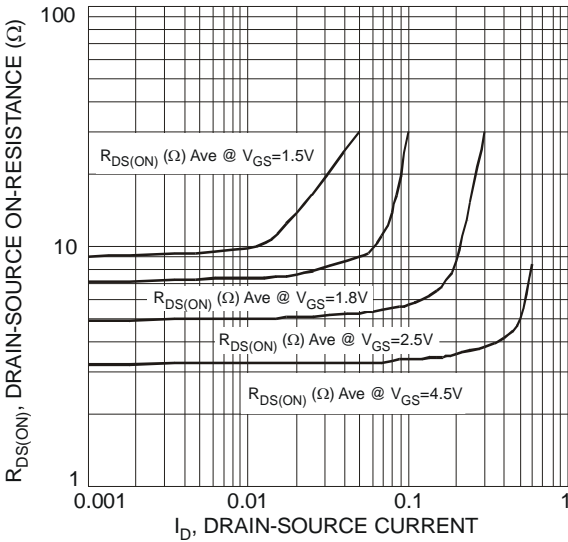


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

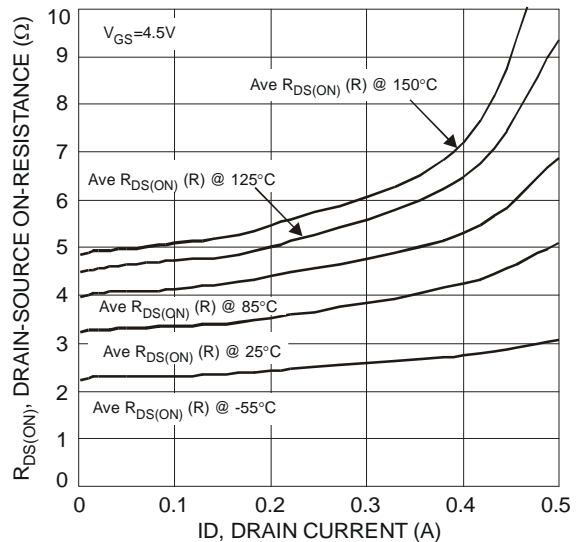


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

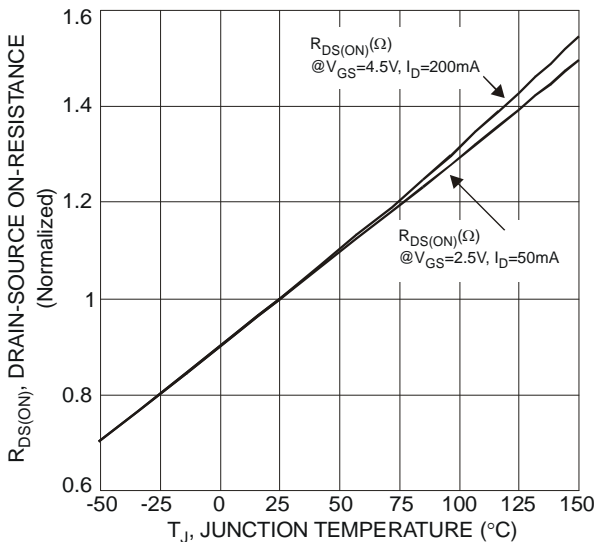


Fig. 5 On-Resistance Variation with Temperature

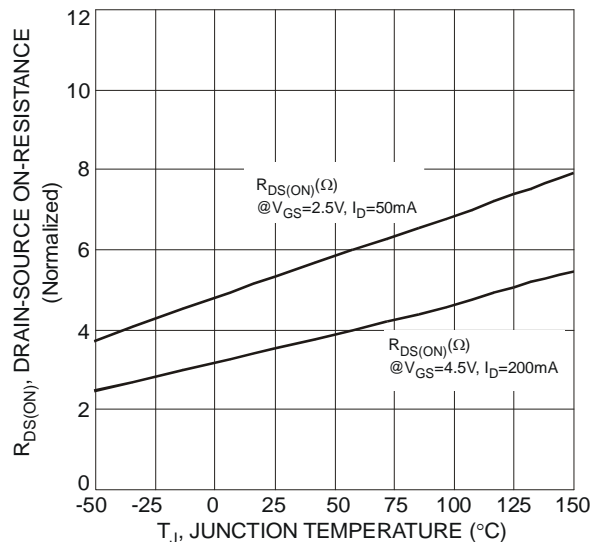


Fig. 6 On-Resistance vs. Temperature

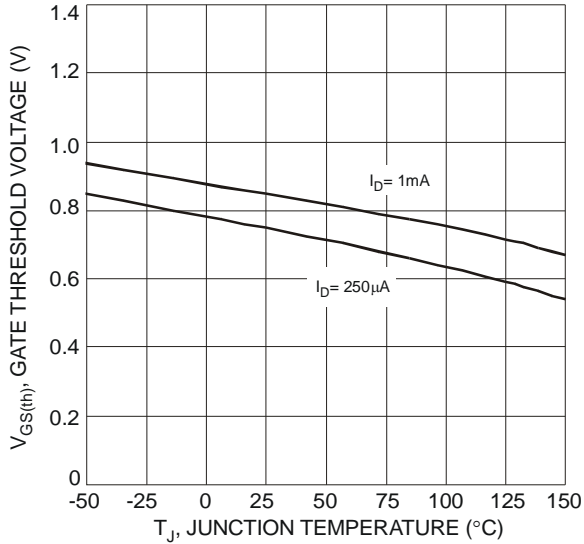


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

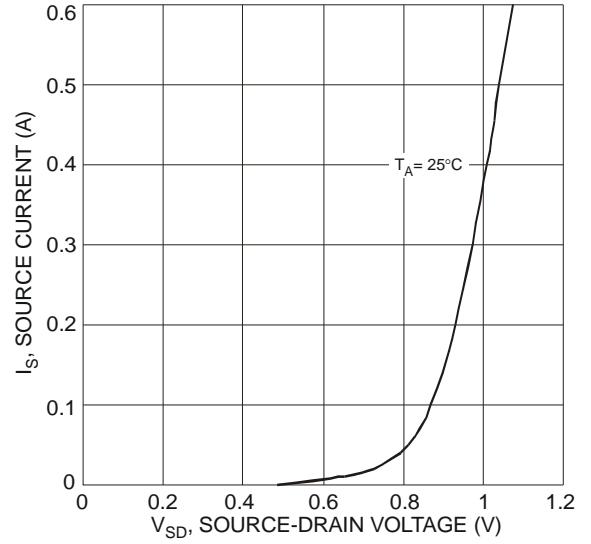


Fig. 8 Diode Forward Voltage vs. Current

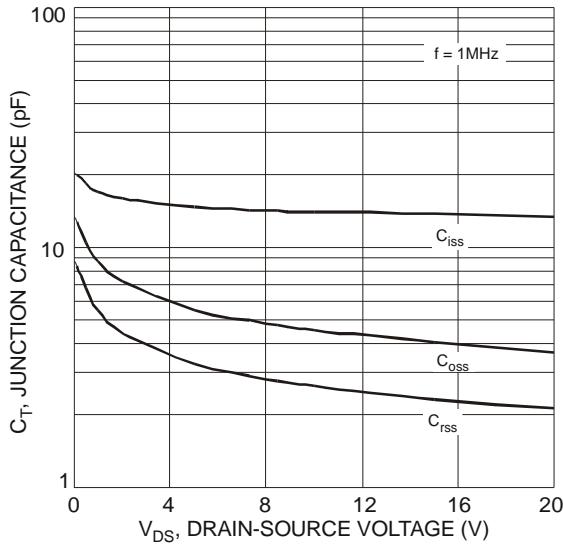


Fig. 9 Typical Junction Capacitance

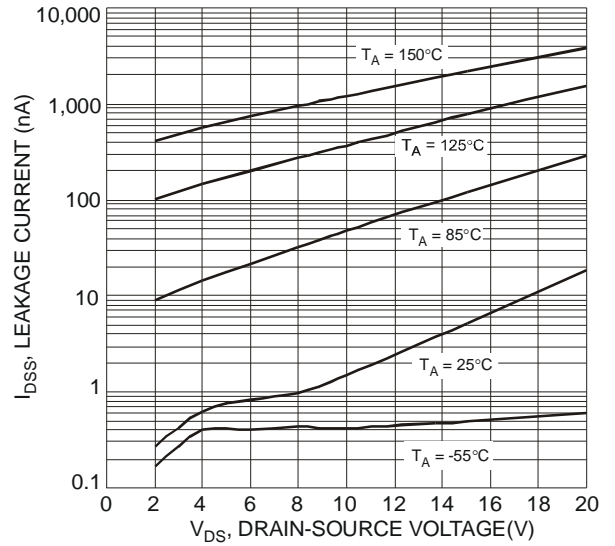


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

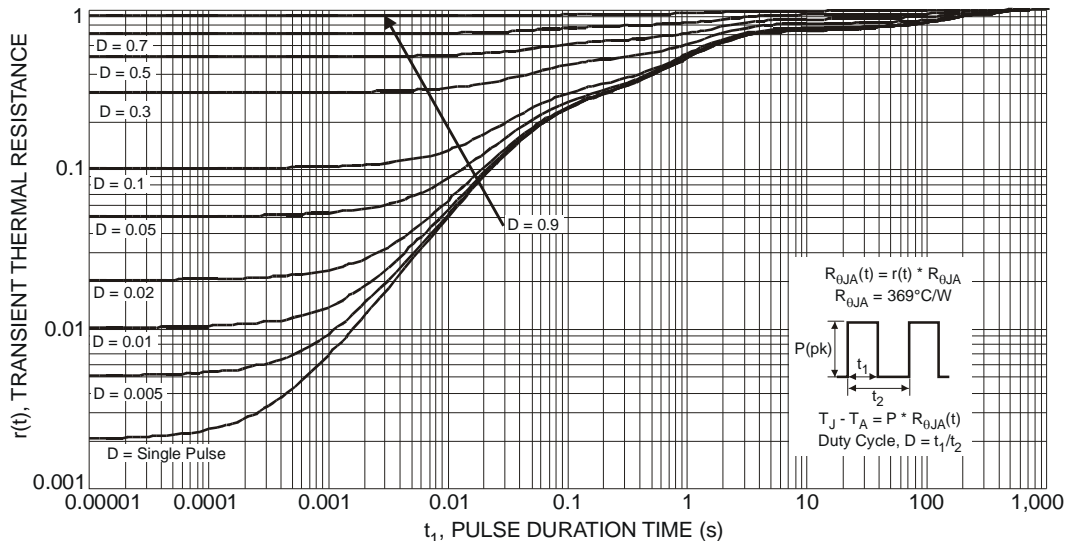
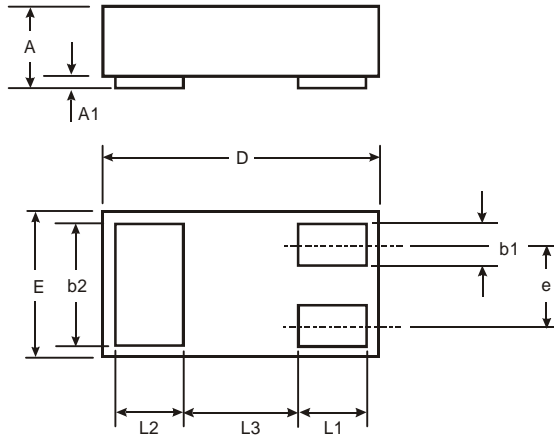


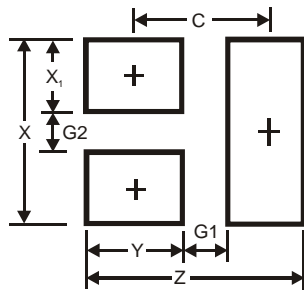
Fig. 11 Transient Thermal Response

**Package Outline Dimensions**



X2-DFN1006-3			
Dim	Min	Max	Typ
A	—	0.40	—
A1	0	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

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